



MMBT5551

NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT5401)
- Ideal for Low Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant
- "Green" Device (Notes 2 and 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

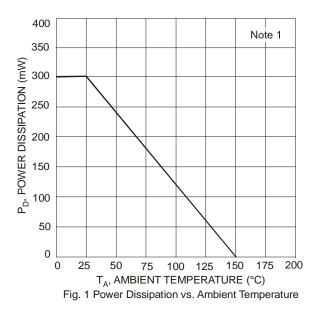
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead. Halogen and Antimony Free.
- 3. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180	_	V	$I_C = 100 \mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160		V	$I_C = 1.0 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_E = 10\mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}		50	nA μA	$V_{CB} = 120V, I_E = 0$ $V_{CB} = 120V, I_E = 0, T_A = 100^{\circ}C$		
Emitter Cutoff Current	I _{EBO}	_	50	nA	$V_{EB} = 4.0V, I_{C} = 0$		
ON CHARACTERISTICS (Note 4)							
		80	_		$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$		
DC Current Gain	h _{FE}	80	250	_	$I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V}$		
		30			$I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.15 0.20	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$		
			0.20		$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1.0	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$		
SMALL SIGNAL CHARACTERISTICS				•			
Output Capacitance	C_{obo}		6.0	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$		
Small Signal Current Gain	h _{fe}	50	250	_	$V_{CE} = 10V, I_{C} = 1.0mA,$ f = 1.0kHz		
Current Gain-Bandwidth Product	f _T	100	300	MHz	$V_{CE} = 10V, I_{C} = 10mA,$ f = 100MHz		
Noise Figure	nF	_	8.0	dB	$V_{CE} = 5.0V$, $I_{C} = 200\mu A$, $R_{S} = 1.0k\Omega$, $f = 1.0kHz$		

Notes: 4. Short duration pulse test used to minimize self-heating effect.



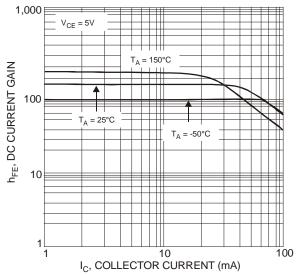
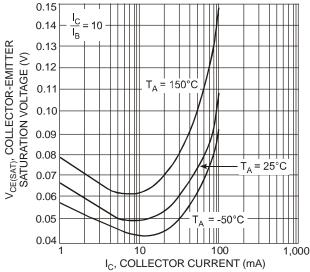
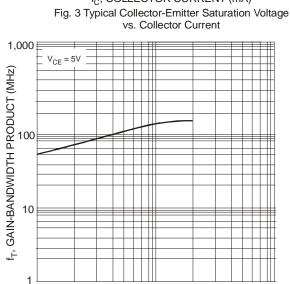


Fig. 2 Typical DC Current Gain vs. Collector Current





vs. Collector Current



10 I_C, COLLECTOR CURRENT (mA)

Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current

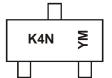
 $V_{\text{BE}(\text{ON})}$, BASE-EMITTER TURN-ON VOLTAGE (V) $V_{CE} = 5V$ 0.9 T_A = -50°C 0.8 0.7 0.6 0.5 $T_A = 150$ °C 0.2 0.1 100 I_C, COLLECTOR CURRENT (mA) Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

Ordering Information (Note 5)

Part Number	Case	Packaging
MMBT5551-7-F	SOT-23	3000/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf. Notes:

Marking Information



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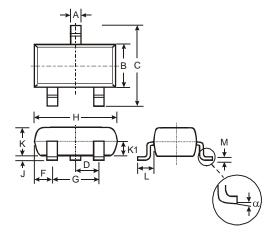
K4N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002)M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	M	N	Р	R	S	Т	U	V	W	Х	Υ	Z	Α	В	С
Month	Jar	1	Feb	Ma	r	Apr	May	у	Jun	Jul		Aug	Sep)	Oct	Nov	,	Dec

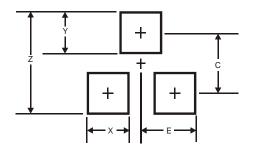


Package Outline Dimensions



	SOT-23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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